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116 and ((remov\$4 or etch\$4)near10 trench\$4)	1

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116 and ((remov\$4 or etch\$4)near10
trench\$4)

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USPT	116 and ((remov\$4 or etch\$4)near10 trench\$4)	1	<u>L17</u>
USPT	115 and 112	2	<u>L16</u>
USPT	16 and 18	2	<u>L15</u>
USPT	19 near6 cool\$4	3907	<u>L14</u>
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USPT	16 and 110	2	<u>L11</u>
USPT	18 same 19	119	<u>L10</u>
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USPT	backside near10 pressure	1517	<u>L8</u>
USPT	16 and \$s7951	0	<u>L7</u>
USPT	15 and 14	59	<u>L6</u>
USPT	11 and 13	62	<u>L5</u>
USPT	photoresist or pattern\$4	511547	<u>L4</u>
USPT	12 or oxide or nitride	452697	<u>L3</u>
USPT	((((borosilicate)or (borosilicate adj4 glass)or (borophosphosilicate adj4 glass))or (TEOS)or (tetraethylorthosilicate))or (hard adj3 mask\$3)) or (BSG or BPSG))	25217	<u>L2</u>
USPT	((((((((semiconduct\$4)and (plasma near8 chamber))and (wafer\$1 or substrate\$1))and (clamp\$4))and (electrode\$1))and (chlorine or "Cl.sub.2"))and (("BCl.sub.3")or (boron adj chloride)or (boron adj trichloride)))and (oxygen or (boron adj trichloride)))and (Argon or "Ar")) and (nitrogen or "N.sub.2"))	62	<u>L1</u>